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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/609,015	06/27/2003	Jozef Szlufcik	IMEC306.001AUS	IMEC306.001AUS 8356	
20995	7590 05/02/2006		EXAMINER		
KNOBBE MARTENS OLSON & BEAR LLP 2040 MAIN STREET			VINH, LAN		
FOURTEENTH FLOOR			ART UNIT	PAPER NUMBER	
IRVINE, CA	92614	1765			
			DATE MAILED: 05/02/2000	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	-
	10/609,015	SZLUFCIK ET AL.	
Office Action Summary	Examiner	Art Unit	-
	Lan Vinh	1765	_
 The MAILING DATE of this communication app Period for Reply 	ears on the cover sheet with the c	orrespondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v - Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing - earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).	
Status			
 1) Responsive to communication(s) filed on <u>07 Ag</u> 2a) This action is FINAL. 2b) This 3) Since this application is in condition for allower closed in accordance with the practice under Egg 	action is non-final.		
Disposition of Claims			
4) ☐ Claim(s) <u>1,5,6,8-15,25-29 and 31-33</u> is/are per 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) <u>1,5,6,8-10,13,25-29 and 31-33</u> is/are 7) ☐ Claim(s) <u>11,12,14 and 15</u> is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or Application Papers	vn from consideration.		
9)☐ The specification is objected to by the Examine	r		
10) The drawing(s) filed on is/are: a) access and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Ex	epted or b) objected to by the liderawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). sected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119			
a) ☐ All b) ☐ Some * c) ☐ None of: 1. ☐ Certified copies of the priority documents 2. ☐ Certified copies of the priority documents 3. ☐ Copies of the certified copies of the priority documents * See the attached detailed Office action for a list	s have been received. s have been received in Applicati ity documents have been receive I (PCT Rule 17.2(a)).	on No ed in this National Stage	
Attachment(s)			
Notice of References Cited (PTO-892)	4) Interview Summary		
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) B) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	atent Application (PTO-152)	

DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 4/7/2006 has been entered.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1, 5-6, 8, 13, 25-29 are rejected under 35 U.S.C. 102(e) as being anticipated by Masuko et al (US 2002/0034611A1)

Masuko discloses a process for forming a pattern on a substrate. The process comprises the steps of: applying an alkaline etching solution (potassium hydroxide) to an inorganic powder dispersed paste layer 21 of the silicon substrate 11, the paste layer comprises a binder/thickener and a solvent (col 4, paragraph 0083, 0091; col 5,

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paragraph 0104; col 8, paragraph 0166; fig. 4f), which reads on applying an a caustic etching paste comprising an etchant and a thickener to a part or a layer of the substrate, wherein the semiconductor substrate is a microcrystalline silicon substrate and wherein the etchant is a water-based potassium hydroxide

heating the substrate such as the part of the layer of the substrate upon which the etching paste has been applied is patterned/etched (col 11, paragraph 0215; col 14, paragraph 0269; fig.4i)

Regarding claims 5-6. Masuko discloses the etching paste includes solvent, binder thickener (col 4, paragraph 0091), which reads on the etching paste comprises a natural etching paste/natural synthetic paste

Regarding claims 8, 13, Masuko discloses that the paste 21 is applied selectively to a major surface and one edge of the substrate to form a pattern of applied paste (col 3, paragraph 0061; fig. 4g)

The limitations of claims 25, 28-29 have been discussed above

Regarding claims 26-27, Masuko discloses that the etching solution/developer comprises of ammonium hydroxide, sodium hydroxide (col 8, paragraph 0161, 0168)

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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4. Claims 9-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Masuko et al (US 2002/0034611A1) in view of Klein et al (US 2003/0160026 A1)

Masuko method has been described above. Unlike the instant claimed inventions as per claims 9-10, Masuko fails to specifically disclose using screen-printing/selective deposition method to apply the etching paste

Klein discloses a method for etching a semiconductor substrate comprises a step of applying an etching paste using screen-printing/selective deposition method (col 4, paragraph 0100)

One skilled in the art at the time the invention was made would have found it obvious to modify Masuko method by using screen-printing/selective deposition method to apply the etching paste as per Klein because Klein discloses that screen-printing is a suitable technique for applying the etching paste as desired (col 4, paragraph 0100)

5. Claims 31-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Masuko et al (US 2002/0034611A1) in view of Klein et al (US 2003/0160026 A1)

Masuko method has been described above. Unlike the instant claimed inventions as per claims 31-33, Masuko fails to specifically disclose using carboxyalkylcellulose salt as a thickener

Klein (US 2003/0160026 A1) also discloses that the etching paste comprises a solvent such as water (col 3, paragraph 0059) and a thickener such as sodium carboxymethylhydroxyethyl cellulose, starch derivative (col 4, paragraph 0071, 0072)

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One skilled in the art at the time the invention was made would have found it obvious to modify Masuko method by using sodium carboxymethylhydroxyethyl cellulose as a thickener as per Klein because Klein discloses that sodium carboxymethylhydroxyethyl cellulose is a possible thickener and the etching paste is completely homogeneous with addition of thickener (col 3, paragraph 0068)

Allowable Subject Matter

6. Claims 11-12, 14-15 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

Regarding claims 11, 14, the cited prior art of record, taken alone or in combination, fails to disclose or suggest a method for etching a semiconductor substrate comprises a step of doping a region of the substrate to yield a do/ed region of the substrate, wherein the step of doping is conducted before the step of applying an etching paste, and wherein the step of applying an etching paste comprises applying an etching paste to the doped region of the substrate/ forming at least one metal contact on an emitter region of the substrate, in combination with the rest of the limitations of claims 11, 14

Response to Arguments

7. Applicant's arguments with respect to rejection(s) of claims 1-6, 8-13, 25-33 based on Klein et al (US 2003/0160026) in view of Williams (US 6,594,542) and Skorupshi (US 2002/016221) have been considered but are moot in view of the new ground(s) of rejection.

The applicants argue that there is no teaching, suggestion, or motivation to substitute ammonium hydroxide, as taught by Skorupshi, or any of the other recited etchants for the ammonium (bi)fluoride etchants of Klein because substimting a strong base etchant for an acidic fluoride-containing etchant clearly changes the principle of operation of the etching media of Klein. This argument is moot in view of the new ground of rejection based on Masuko et al (US 2002/0034611A1) since Masuko discloses a process for forming a pattern on a substrate by applying an alkaline etching/developer solution contains ammonium hydroxide (col 8, paragraph 0161, 0168)

Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 571 272 1471. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 571 272 1465. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

LV

April 25, 2006